

HZU Series

Silicon Planar Zener Diode for Stabilizer

REJ03G0625-0900 Rev.9.00 Jul 06, 2006

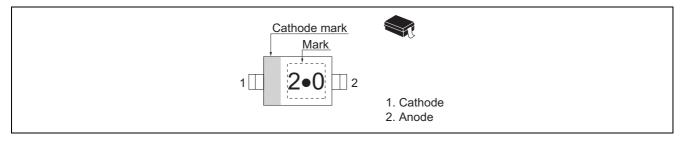
Features

- These diodes are delivered taped.
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Name	Package Code	
HZU Series	Let to Mark Code	URP	PTSP0002ZA-A	

Pin Arrangement





Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Symbol	Value	Unit
Pd * ¹	200	mW
Тј	150	°C
Tstg	-55 to +150	°C
	Pd * ¹ Tj	Pd *1 200 Tj 150

Note: 1. With P.C. Board.

Electrical Characteristics

			Zener Volta	ge	Rever	se Current	Dynami	c Resistance
				Test		Test		Test
		Vz	(V) * ¹	Condition	I _R (μΑ)	Condition	r _d (Ω)	Condition
Туре	Grade	Min	Max	I _Z (mA)	Max	V _R (V)	Max	I _Z (mA)
HZU2.0	В	1.90	2.20	5	120	0.5	100	5
HZU2.2	В	2.10	2.40	5	120	0.7	100	5
HZU2.4	В	2.30	2.60	5	120	1.0	100	5
HZU2.7	В	2.50	2.90	5	120	1.0	110	5
	B1	2.50	2.75					
	B2	2.65	2.90					
HZU3.0	В	2.80	3.20	5	50	1.0	120	5
	B1	2.80	3.05					
	B2	2.95	3.20					
HZU3.3	В	3.10	3.50	5	20	1.0	130	5
	B1	3.10	3.35					
	B2	3.25	3.50					
HZU3.6	В	3.40	3.80	5	10	1.0	130	5
	B1	3.40	3.65					
	B2	3.55	3.80					
HZU3.9	В	3.70	4.10	5	10	1.0	130	5
	B1	3.70	3.97					
	B2	3.87	4.10					
HZU4.3	В	4.01	4.48	5	10	1.0	130	5
	B1	4.01	4.21					
	B2	4.15	4.34					
	B3	4.28	4.48					
HZU4.7	В	4.42	4.90	5	10	1.0	130	5
	B1	4.42	4.61					
	B2	4.55	4.75					
	B3	4.69	4.90					
HZU5.1	В	4.84	5.37	5	5	1.5	130	5
	B1	4.84	5.04					
	B2	4.98	5.20]				
	B3	5.14	5.37	1				
HZU5.6	В	5.31	5.92	5	5	2.5	80	5
	B1	5.31	5.55]				
	B2	5.49	5.73	1				
	B3	5.67	5.92					

Note: 1. Tested with pulse ($P_W = 40 \text{ ms}$)



			Zener Volt	age	Rever	se Current	Dynamic Resistance	
		V ₇	(V) * ¹	Test Condition	Ι _R (μΑ)	Test Condition	r _d (Ω)	Test Condition
Туре	Grade	Min	Max	I _z (mA)	Max	V _R (V)	Max	I _z (mA)
HZU6.2	В	5.86	6.53	5	2	3.0	50	5
	B1	5.86	6.12					
ľ	B2	6.06	6.33					
	B3	6.26	6.53					
HZU6.8	В	6.47	7.14	5	2	3.5	30	5
	B1	6.47	6.73					
	B2	6.65	6.93	-				
	B3	6.86	7.14	-				
HZU7.5	B	7.06	7.84	5	2	4.0	30	5
	B1	7.06	7.36	-				
	B2	7.28	7.60					
	B3	7.52	7.84					
HZU8.2	B	7.76	8.64	5	2	5.0	30	5
	B1	7.76	8.10	1		0.0		
-	B1 B2	8.02	8.36	1				
	B3	8.28	8.64	-				
HZU9.1	B	8.56	9.55	5	2	6.0	30	5
-	B1	8.56	8.93		2	0.0	00	5
	B2	8.85	9.23	-				
	B2 B3	9.15	9.55	-				
HZU10	B	9.45	10.55	5	2	7.0	30	5
	B1	9.45	9.87		2	7.0	50	5
	B1 B2	9.77	10.21	-				
	B2 B3	10.11	10.55	-				
HZU11	B	10.11	11.56	5	2	8.0	30	5
112011	B1	10.44	10.88	5	2	0.0	30	5
	B1 B2	10.44	11.22	-				
	B2 B3	11.10	11.56	-				
HZU12	B	11.10	12.60	5	2	9.0	25	5
112012	B1			5	2	9.0	35	5
		11.42 11.74	11.90	-				
	B2		12.24	-				
HZU13	B3 B	12.08	12.60	5	2	40.0	05	5
112013		12.47	13.96	5	2	10.0	35	S
	B1	12.47	13.03	-				
	B2	12.91	13.49	4				
	B3	13.37	13.96		-	44.0	40	
HZU15	B	13.84	15.52	5	2	11.0	40	5
	B1	13.84	14.46	4				
	B2	14.34	14.98	-				
	B3	14.85	15.52	_			10	_
HZU16	B	15.37	17.09	5	2	12.0	40	5
	B1	15.37	16.01	4				
	B2	15.58	16.51	4				
	B3	16.35	17.09					
HZU18	В	16.94	19.03	5	2	13.0	45	5
	B1	16.94	17.70	4				
	B2	17.56	18.35	4				
	B3	18.21	19.03					

Note: 1. Tested with pulse ($P_W = 40 \text{ ms}$)



			Zener Voltage		Revers	se Current	Dynamic	Dynamic Resistance	
		V _z ((V)* ¹	Test Condition	Ι _R (μΑ)	Test Condition	r _d (Ω)	Test Condition	
Туре	Grade	Min	Max	I _Z (mA)	Max	V _R (V)	Max	I _Z (mA)	
HZU20	В	18.86	21.08	5	2	15.0	50	5	
	B1	18.86	19.70						
	B2	19.52	20.39						
	B3	20.21	21.08						
HZU22	В	20.88	23.17	5	2	17.0	55	5	
	B1	20.88	21.77						
	B2	21.54	22.47						
	B3	22.23	23.17						
HZU24	В	22.93	25.57	5	2	19.0	60	5	
	B1	22.93	23.96						
	B2	23.72	24.78						
	B3	24.54	25.57						
HZU27	В	25.10	28.90	2	2	21.0	70	2	
HZU30	В	28.00	32.00	2	2	23.0	80	2	
HZU33	В	31.00	35.00	2	2	25.0	80	2	
HZU36	В	34.00	38.00	2	2	27.0	90	2	

Note: 1. Tested with pulse ($P_W = 40 \text{ ms}$).



Mark Code

Туре	Grade	Mark No.	Туре	Grade	Mark No.	Туре	Grade	Mark No.
HZU2.0	В	2 · 0	HZU6.2	B1	6 · 2	HZU13	B1	1 3 ·
HZU2.2	В	2 · 2		B2	6 · 2		B2	1 3 ·
HZU2.4	В	2 · 4		B3	6 · 2		B3	1 3 ·
HZU2.7	B1	2 · 7	HZU6.8	B1	6 · 8	HZU15	B1	1 5 ·
	B2	2 · 7		B2	6 · 8		B2	1 5 ·
HZU3.0	B1	3 · 0		B3	6 · 8		B3	1 5 ·
	B2	3 · 0	HZU7.5	B1	7 · 5	HZU16	B1	1 6 ·
HZU3.3	B1	3 · 3		B2	7 · 5		B2	1 6 ·
	B2	3 · 3		B3	7 · 5		B3	1 6 ·
HZU3.6	B1	3 · 6	HZU8.2	B1	8 · 2	HZU18	B1	1 8 ·
	B2	3 · 6		B2	8 · 2		B2	1 8 ·
HZU3.9	B1	3 · 9		B3	8 · 2		B3	1 8 ·
	B2	3 · 9	HZU9.1	B1	9 · 1	HZU20	B1	20.
HZU4.3	B1	4 · 3		B2	9 · 1		B2	20.
	B2	4 · 3		B3	9 · 1		B3	20.
	B3	4 · 3	HZU10	B1	10.	HZU22	B1	22.
HZU4.7	B1	4 · 7		B2	10.		B2	22.
	B2	4 · 7		B3	10.		B3	22.
	B3	4 · 7	HZU11	B1	11.	HZU24	B1	24.
HZU5.1	B1	5 · 1		B2	11.		B2	24.
	B2	5 · 1		B3	11.		B3	24.
	B3	5 · 1	HZU12	B1	12.	HZU27	В	27.
HZU5.6	B1	5 · 6		B2	12.	HZU30	В	30.
	B2	5 · 6		B3	12.	HZU33	В	33.
	B3	5 · 6				HZU36	В	36.
Notes: 1.	Example of	Marking					•	
(1)	One grade ty	pe (B)	(2) Two grade ty	/pe (B1,B2)		ade type (B1,B2,E Jpper		ower
Ш	2•0 🔲 🛛	30•]] HZU30B	HZU3.0B1	3•0 HZU3.0B2	HZU4.3B1	1 [4•3]		
0	The smede F		from B1 min to					

2. The grade B type includes from B1 min. to B3 (or B2) max.

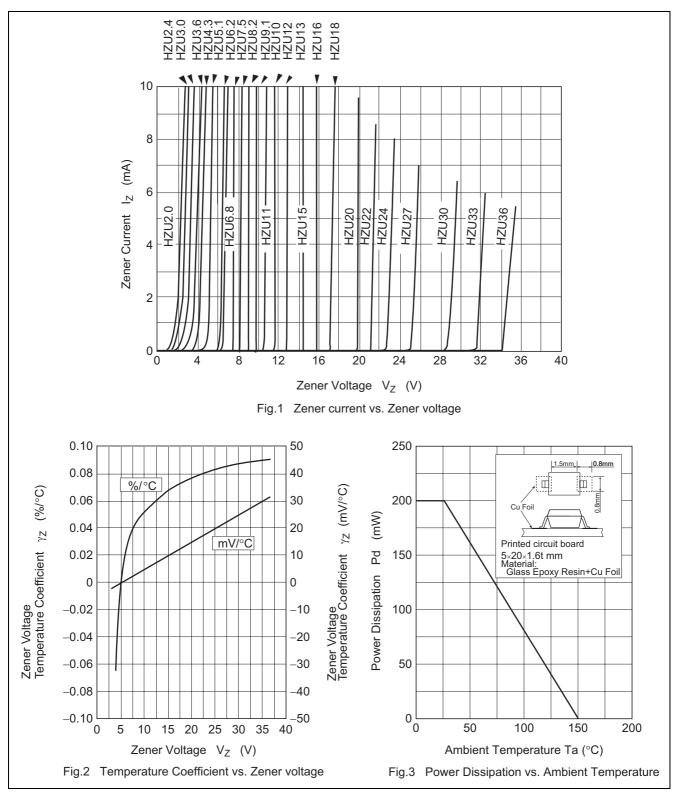
3. B grade is standard and has better delivery, these are marked one of B1, B2, B3.

4. Type No. is as follows; HZU2.0B, HZU2.2B, ••• HZU36B. (B grade)

5. Type No. is as follows; HZU2.7B1, HZU2.7B2, ••• HZU24B3. (B 1, B2, B3 grade)

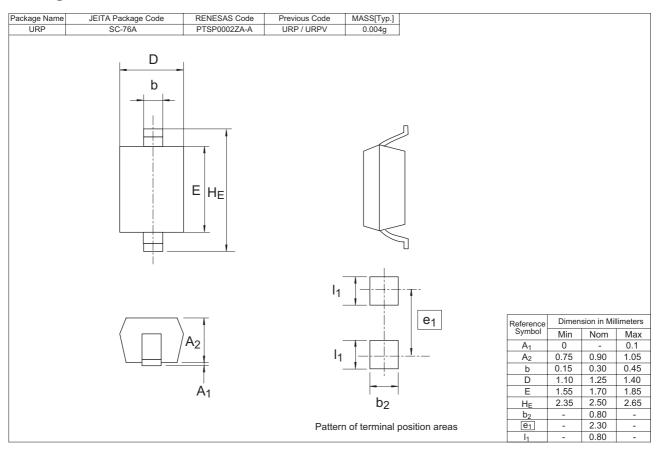


Main Characteristic





Package Dimensions





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